Product Overview

FGH75T65SQDTL4: IGBT, 650 V, 75 A Field Stop Trench

For complete documentation, see the data sheet.

Using novel field stop IGBT technology, ON semiconductor's new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential

Features

- Maximum Junction Temperature: T_J = 175°C
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)}$ = 1.6 V (Typ.) @ I_C = 75 A
- 100% of the Parts tested for I_{LM}(1)
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

Part Electrical Specifications

Product	Compliance	Status	$V_{(BR)CES}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (µs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
FGH75T65SQDTL4	Pb-free Halide free	Active	650	75	1.6	1.8	0.266	0.307	76	-	128	-	-	375	Yes	TO-247-4

For more information please contact your local sales support at www.onsemi.com.

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